

## AMENDMENTS TO THE CLAIMS

Please amend Claims 16-19 as follows.

### **LISTING OF CLAIMS**

1.-15. (cancelled)

16. (currently amended) A method of manufacturing a semiconductor, comprising steps of:

forming a basic structure of a semiconductor device on a semiconductor wafer;

forming a final passivation film that transmits ultra violet rays on an uppermost of the basic structure;

applying a bias voltage to the semiconductor device, ~~the bias voltage having a predetermined level voltage that can maintain the semiconductor device with turning of f; and ;~~

maintaining the bias voltage for a first predetermined time at a predetermined level to maintain the semiconductor device in an off state; and

radiating ultra violet rays to the basic structure of the semiconductor device through the final passivation film for a second predetermined time after the step of ~~applying~~ the bias voltage.

17. (currently amended; withdrawn) A method of manufacturing a semiconductor device, ~~comprising steps of~~ according to Claim 1, further comprising:

~~forming a basic structure of a semiconductor device on a semiconductor wafer;~~

~~forming a final passivation film that transmits ultra violet rays on an uppermost of the basic structure;~~

~~dividing the semiconductor device into a plurality of semiconductor chips;~~  
and

mounting each of the semiconductor ~~[[chip]]~~ chips on a package having a transmitting portion that can transmit ultra violet rays at least on the final passivation film side~~[[;]]~~.

~~applying a bias voltage to the semiconductor device, the bias voltage having a predetermined level voltage that can maintain the semiconductor device with turning off; and~~

~~radiating ultra violet rays to the basic structure of the semiconductor device through the transmitting portion and the final passivation film after the step of applying the bias voltage.~~

18. (currently amended) A method of manufacturing a semiconductor according to Claim 16, wherein:

the semiconductor is a switching element selected from one of a LDMOS FET (Lateral Double-Diffused Metal Oxide Semiconductor Field effect Transistor) and a VDMOS FET (Vertical Double-Diffused Metal Oxide Semiconductor Field effect Transistor); and

the bias voltage applying step ~~applies~~ comprises applying the bias voltage between a source and a drain of the switching element.

19. (currently amended) A method of manufacturing a semiconductor according to Claim 16, wherein the ultra violet rays radiation step ~~radiates~~ comprises radiating ultra violet rays having a band whose wave length of 253.7 nm.

20. (withdrawn) A method of manufacturing a semiconductor according to Claim 17, wherein:

the semiconductor is a switching element selected from one of a LDMOS FET (Lateral Double-Diffused Metal Oxide Semiconductor Field effect Transistor) and a VDMOS FET (Vertical Double-Diffused Metal Oxide Semiconductor Field effect Transistor); and

the bias voltage applying step applies the bias voltage between a source and a drain of the switching element.

21. (withdrawn) A method of manufacturing a semiconductor according to Claim 17, wherein the ultra violet rays radiation step radiates ultra violet rays having a band whose wave length of 253.7 nm.

22. (previously presented) A method of manufacturing a semiconductor device according to Claim 16, wherein the step of forming the basic structure includes:

forming a transistor structure, formed in a semiconductor substrate defined in said semiconductor wafer, comprising a drain region, a source region formed in a channel well layer and a gate electrode, formed on the semiconductor substrate, with a gate oxide film interposed between said gate electrode and a channel forming region formed in said channel well layer, said transistor structure further comprising an insulating isolation film formed between said drain region and said channel well layer, wherein:

the gate electrode is formed so as to extend toward the drain region to have a portion overlapping with the insulating isolation film, and said gate electrode is formed so that a maximum electric field point in the neighborhood of a surface of the semiconductor substrate occurs at substantially the center portion of a region corresponding to the insulating isolation film, when a predetermined bias voltage is applied between the source region and the drain region, and the source region and the gate electrode are at substantially identical potential.

23. (previously presented) A method of manufacturing a semiconductor device according to Claim 16, wherein the step of forming the basic structure includes:

forming a transistor structure, formed in a semiconductor substrate defined in said semiconductor wafer, comprising a drain region, a source region formed in a channel well layer and a gate electrode, formed on the semiconductor substrate, with a gate oxide film interposed between said gate electrode and a channel forming region formed in said channel well layer, said transistor structure further comprising an

insulating isolation film formed between said drain region and said channel well layer, wherein:

the gate electrode extends toward the drain region so as to have a portion overlapping with the insulating isolation film, and said gate electrode is formed so that a peak carrier generation rate in the neighborhood of a surface of the semiconductor substrate occurs at lower region corresponding to the insulating isolation film, when a predetermined bias voltage is applied between the source region and the drain region, and the source region and the gate electrode are at substantially identical potential.

24. (previously presented) A method of manufacturing a semiconductor device according to Claim 16, wherein the step of forming the basic structure includes:

forming a transistor structure, formed in a semiconductor substrate defined in said semiconductor wafer, comprising a drain region, a source region formed in a channel well layer and a gate electrode, formed on the semiconductor substrate, with a gate oxide film interposed between said gate electrode and a channel forming region formed in said channel well layer, said transistor structure further comprising an insulating isolation film formed between said drain region and said channel well layer, wherein:

the gate electrode extends toward the drain region so as to have a portion overlapping with the insulating isolation film, and said gate electrode is formed so that a carrier flow in the neighborhood of a surface of the semiconductor substrate contains a component toward an opposite side direction of the insulating isolation film, when a

predetermined bias voltage is applied between the source region and the drain region, and the source region and the gate electrode are at substantially identical potential.

25. (previously presented) A method of manufacturing a semiconductor device according to Claim 22, wherein said gate electrode is formed so that a protrusion amount onto the insulating isolation film is set equal to or more than substantially a half of a width size of the insulating isolation film.

26. (previously presented). A method of manufacturing a semiconductor device according to Claim 23, wherein said gate electrode is formed so that a protrusion amount onto the insulating isolation film is set equal to or more than substantially a half of a width size of the insulating isolation film.

27. (previously presented) A method of manufacturing a semiconductor device according to Claim 24, wherein said gate electrode is formed so that a protrusion amount onto the insulating isolation film is set equal to or more than substantially a half of a width size of the insulating isolation film.

28. (previously presented) A method of manufacturing a semiconductor device according to Claim 25, wherein said gate electrode is formed so that a protrusion amount onto the insulating isolation film is set equal to substantially a half of a width size of the insulating isolation film.

29. (previously presented) A method of manufacturing a semiconductor device according to Claim 26, wherein said gate electrode is formed so that a protrusion amount onto the insulating isolation film is set equal to substantially a half of a width size of the insulating isolation film.

30. (previously presented) A method of manufacturing a semiconductor device according to Claim 27, wherein said gate electrode is formed so that a protrusion amount onto the insulating isolation film is set equal to substantially a half of a width size of the insulating isolation film.

31. (previously presented) A method of manufacturing a semiconductor device according to Claim 22, wherein the step of forming the basic structure includes:

preparing an SOI substrate wafer formed from a supporting substrate and a semiconductor layer with an insulating film interposed therebetween, wherein said transistor structure is formed in said semiconductor layer.

32. (previously presented) A method of manufacturing a semiconductor device according to Claim 31, wherein the supporting substrate is made of semiconductor material, and the supporting substrate includes a potential fixing electrode formed on its back surface to fix a potential of the supporting substrate with a predetermined level.

33. (previously presented) A method of manufacturing a semiconductor device according to Claim 16, wherein the step of forming the basic structure includes:

forming a transistor structure, formed in a semiconductor substrate defined in said semiconductor wafer, comprising a drain region having a P-type conductivity, a source region, formed in a channel well layer of a N-type conductivity, having a P-type conductivity, and a gate electrode, formed on the semiconductor substrate, with a gate oxide film interposed between said gate electrode and a channel forming region formed in said channel well layer, said transistor structure further comprising an insulating isolation film formed between said drain region and said channel well layer, wherein:

the gate electrode is disposed at a side of said insulating isolation film opposite to a location where the drain region is formed, the gate electrode extends toward the drain region so as to have a portion overlapping with the insulating isolation film, and said gate electrode is formed so that a maximum electric field point in the neighborhood of a surface of the semiconductor substrate occurs at substantially the center portion of a region corresponding to the insulating isolation film, when a predetermined bias voltage is applied between the source region and the drain region, and the source region and the gate electrode are at substantially identical potential.

34. (withdrawn) A method of manufacturing a semiconductor device according to Claim 17, wherein the step of forming the basic structure includes:

forming a transistor structure, formed in a semiconductor substrate defined in said semiconductor wafer, comprising a drain region, a source region formed



in a channel well layer and a gate electrode, formed on the semiconductor substrate, with a gate oxide film interposed between said gate electrode and a channel forming region formed in said channel well layer, said transistor structure further comprising an insulating isolation film formed between said drain region and said channel well layer, wherein:

the gate electrode is formed so as to extend toward the drain region to have a portion overlapping with the insulating isolation film, and said gate electrode is formed so that a maximum electric field point in the neighborhood of a surface of the semiconductor substrate occurs at substantially the center portion of a region corresponding to the insulating isolation film, when a predetermined bias voltage is applied between the source region and the drain region, and the source region and the gate electrode are at substantially identical potential.

35. (withdrawn) A method of manufacturing a semiconductor device according to Claim 17, wherein the step of forming the basic structure includes:

forming a transistor structure, formed in a semiconductor substrate defined in said semiconductor wafer, comprising a drain region, a source region formed in a channel well layer and a gate electrode, formed on the semiconductor substrate, with a gate oxide film interposed between said gate electrode and a channel forming region formed in said channel well layer, said transistor structure further comprising an insulating isolation film formed between said drain region and said channel well layer, wherein:

the gate electrode extends toward the drain region so as to have a portion overlapping with the insulating isolation film, and said gate electrode is formed so that a peak carrier generation rate in the neighborhood of a surface of the semiconductor substrate occurs at lower region corresponding to the insulating isolation film, when a predetermined bias voltage is applied between the source region and the drain region, and the source region and the gate electrode are at substantially identical potential.

36. (withdrawn) A method of manufacturing a semiconductor device according to Claim 17, wherein the step of forming the basic structure includes:

forming a transistor structure, formed in a semiconductor substrate defined in said semiconductor wafer, comprising a drain region, a source region formed in a channel well layer and a gate electrode, formed on the semiconductor substrate, with a gate oxide film interposed between said gate electrode and a channel forming region formed in said channel well layer, said transistor structure further comprising an insulating isolation film formed between said drain region and said channel well layer, wherein:

the gate electrode extends toward the drain region so as to have a portion overlapping with the insulating isolation film, and said gate electrode is formed so that a carrier flow in the neighborhood of a surface of the semiconductor substrate contains a component toward an opposite side direction of the insulating isolation film, when a predetermined bias voltage is applied between the source region and the drain region, and the source region and the gate electrode are at substantially identical potential.

37. (withdrawn) A method of manufacturing a semiconductor device according to Claim 34, wherein said gate electrode is formed so that a protrusion amount onto the insulating isolation film is set equal to or more than substantially a half of a width size of the insulating isolation film.

38. (withdrawn) A method of manufacturing a semiconductor device according to Claim 35, wherein said gate electrode is formed so that a protrusion amount onto the insulating isolation film is set equal to or more than substantially a half of a width size of the insulating isolation film.

39. (withdrawn) A method of manufacturing a semiconductor device according to Claim 36, wherein said gate electrode is formed so that a protrusion amount onto the insulating isolation film is set equal to or more than substantially a half of a width size of the insulating isolation film.

40. (withdrawn) A method of manufacturing a semiconductor device according to Claim 37, wherein said gate electrode is formed so that a protrusion amount onto the insulating isolation film is set equal to substantially a half of a width size of the insulating isolation film.

41. (withdrawn) A method of manufacturing a semiconductor device according to Claim 38, wherein said gate electrode is formed so that a protrusion

amount onto the insulating isolation film is set equal to substantially a half of a width size of the insulating isolation film.

42. (withdrawn) A method of manufacturing a semiconductor device according to Claim 39, wherein said gate electrode is formed so that a protrusion amount onto the insulating isolation film is set equal to substantially a half of a width size of the insulating isolation film.

43. (withdrawn) A method of manufacturing a semiconductor device according to Claim 34, wherein the step of forming the basic structure includes:

preparing an SOI substrate wafer formed from a supporting substrate and a semiconductor layer with an insulating film interposed therebetween, wherein said transistor structure is formed in said semiconductor layer.

44. (withdrawn) A method of manufacturing a semiconductor device according to Claim 43, wherein the supporting substrate is made of semiconductor material, and the supporting substrate includes a potential fixing electrode formed on its back surface to fix a potential of the supporting substrate with a predetermined level.

45. (withdrawn) A method of manufacturing a semiconductor device according to Claim 17, wherein the step of forming the basic structure includes:

forming a transistor structure, formed in a semiconductor substrate defined in said semiconductor wafer, comprising a drain region having a P-type

conductivity, a source region, formed in a channel well layer of a N-type conductivity, having a P-type conductivity, and a gate electrode, formed on the semiconductor substrate, with a gate oxide film interposed between said gate electrode and a channel forming region formed in said channel well layer, said transistor structure further comprising an insulating isolation film formed between said drain region and said channel well layer, wherein:

the gate electrode is disposed at a side of said insulating isolation film opposite to a location where the drain region is formed, the gate electrode extends toward the drain region so as to have a portion overlapping with the insulating isolation film, and said gate electrode is formed so that a maximum electric field point in the neighborhood of a surface of the semiconductor substrate occurs at substantially the center portion of a region corresponding to the insulating isolation film, when a predetermined bias voltage is applied between the source region and the drain region, and the source region and the gate electrode are at substantially identical potential.